

# VHF Variable Capacitance Diode

## FEATURES

- High linearity
- Excellent matching to 1% DMA
- · Very small plastic SMD package
- · C28: 2.5 pF; ratio: 26.

### APPLICATIONS

- Electronic tuning in VHF television tuners, band A up to 160 MHz
- · VCO.

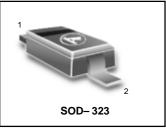
#### DESCRIPTION

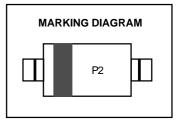
The BB132 is a variable capacitance diode fabricated in planar technology, and encapsulated in the SOD323 very small plastic SMD package.

The excellent matching performance is achieved by gliding matching and a direct matching assembly procedure.



# BB132





### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

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SYMBOL	PARAMETER	MIN.	MAX.	UNIT			
V <sub>R</sub>	continuous reverse voltage	-	30	V			
l <sub>F</sub>	continuous forward current	-	20	mA			
T <sub>stg</sub>	storage temperature	-55	+150	°C			
Tj	operating junction temperature	-55	+125	°C			

## **ELECTRICAL CHARACTERISTICS**

T<sub>j</sub> = 25 °C unless otherwise specified.

PARAMETER	CONDITIONS		MAX.	UNIT
reverse current	VR = 30 V; see Fig.2		10	nA
	VR = 30 V; Tj = 85 °C; see Fig.2		200	nA
diode series resistance	f = 100 MHz; note 1		2	Ω
diode capacitance	Vr = 0.5 V; f = 1 MHz; see Figs 1 and 3		75	рF
	VR = 28 V;f = 1 MHz; see Figs 1 and 3	2.3	2.75	рF
capacitance ratio	f = 1 MHz	24	30	
			4	0/
capacitance matching	(gliding)	_	I	%
	VR= 0.5 to 28 V; in a sequence of 15 diodes	_	2	%
	reverse current diode series resistance diode capacitance	reverse current $V_R = 30 \text{ V}$ ; see Fig.2 $V_R = 30 \text{ V}$ ; Tj = 85 °C; see Fig.2diode series resistancef = 100 MHz; note 1diode capacitance $V_R = 0.5 \text{ V}$ ; f = 1 MHz; see Figs 1 and 3 $V_R = 28 \text{ V}$ ; f = 1 MHz; see Figs 1 and 3capacitance ratiof = 1 MHzcapacitance matching $V_R = 0.5 \text{ to } 28 \text{ V}$ ; in a sequence of 4 diodes (gliding)	reverse current $V_R = 30 \text{ V}$ ; see Fig.2- $V_R = 30 \text{ V}$ ; Tj = 85 °C; see Fig.2-diode series resistancef = 100 MHz; note 1-diode capacitance $V_R = 0.5 \text{ V}$ ; f = 1 MHz; see Figs 1 and 360 $V_R = 28 \text{ V}$ ; f = 1 MHz; see Figs 1 and 32.3capacitance ratiof = 1 MHz24capacitance matching $V_R = 0.5 \text{ to } 28 \text{ V}$ ; in a sequence of 4 diodes- $V_R = 0.5 \text{ to } 28 \text{ V}$ ; in a sequence of 15 diodes-	reverse current $V_R = 30 V$ ; see Fig.2-10 $V_R = 30 V$ ; Tj = 85 °C; see Fig.2-200diode series resistancef = 100 MHz; note 1-2diode capacitance $V_R = 0.5 V$ ; f = 1 MHz; see Figs 1 and 36075 $V_R = 28 V$ ; f = 1 MHz; see Figs 1 and 32.32.75capacitance ratiof = 1 MHz2430capacitance matching $V_R = 0.5$ to 28 V; in a sequence of 4 diodes-1(gliding) $V_R = 0.5$ to 28 V; in a sequence of 15 diodes-2

### Note

1. VR is the value at which Cd = 30 pF.





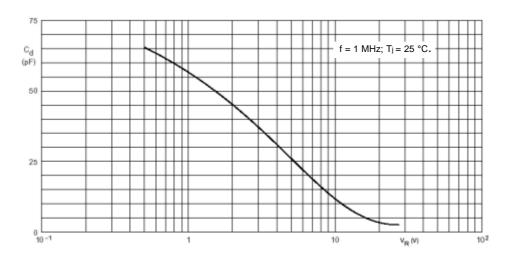


Fig.1 Diode capacitance as a function of reverse voltage; typical values.

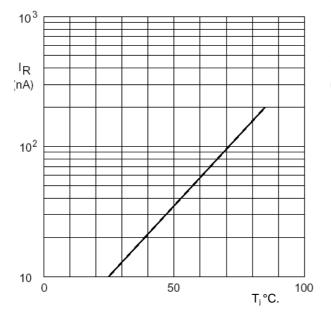


Fig.2 Reverse current as a function of junction temperature; maximum values.

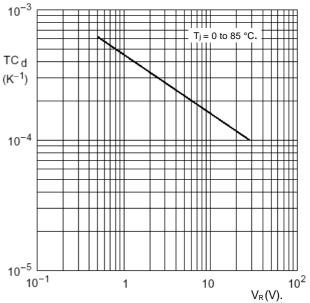


Fig.3 Temperature coefficient of diode capacitance as a function of reverse voltage; typical values.